

EAST Search History

EAST Search History (Prior Art)

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S87	179	(sin OR Si ₃ N ₄ or "Si.sub.3 N.sub.4" or (Silicon adj nitride)) with plasma with CVD with ((resistivity or resistance) or semi\$1insulat\$5)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/13 12:39
S86	62	S85 and @pd>"20090801"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/12 23:41
S85	1492	257/409,488-490.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/12 23:41
S84	16	S83 and gate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/12 23:41

S83	140	(Yano near Mitsuhiro) or (Mochizuki near Kouichi)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/12 23:41
S82	227	S81 and (sin OR SiN or "Si.sub.3 N.sub.4" or si3N4 or (SiLicon adj nitride)) and gate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/12 23:32
S81	1202	(termination or peripheral) with (field adj4 (relie \$6 or relax\$6 or plate))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/12 23:32
S80	90	257/e29.01,e29.006.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/12 23:20
S73	227	S72 and @pd>"20090801"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/12 22:58

S72	4272	257/139,212,34,401,630,646,649.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/12 22:58
S69	188	S66 and (sin OR (SILIcon adj nitride)) and gate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/08/06 12:37
S68	1	S66 and S67	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/08/06 12:36
S67	11850	(sin OR (SILIcon adj nitride)) with plasma with CVD	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/08/06 12:36
S66	1105	(termination or peripheral) with (field adj4 (relie \$6 or relax\$6 or plate))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/08/06 12:36

S65	14	257/e29.01, e29.S49.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/08/06 12:34
S64	117	S61 not S62	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/08/06 12:31
S63	11	"5196354"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/08/06 12:26
S62	16	S61 and gate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/08/06 12:21
S61	133	(Yano near Mitsuhiro) or (Mochizuki near Kouichi)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/08/06 12:21

S60	196	S59 and gate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/08/06 12:09
S59	444	(sin OR (SILIcon adj nitride)) with termination	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/08/06 12:09
S58	1	(sin OR (SILIcon adj nitride)) with plasma with CVD with termination	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/08/06 12:09
S57	18	"5521409"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/08/06 12:04
S56	424	S54 and S55	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/08/06 11:39

S55	5802	(sin OR (SILIcon adj nitride)) with (terminat\$6 or peripheral)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/08/06 11:39
S54	4562	S53 and gate and (terminat\$6 or peripheral)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/08/06 11:38
S53	11850	(sin OR (SILIcon adj nitride)) with plasma with CVD	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/08/06 11:37
S52	17	S51 and terminat\$5	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/08/06 11:32
S51	154	(sin OR (SILIcon adj nitride)) with plasma with CVD with ((resistivity or resistance) or semi \$1insulat\$5)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/08/06 11:32

S50	15	(sin OR (SILIcon adj nitride)) with plasma with CVD with (terminat\$6)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/08/06 11:31
S49	1702023	(sin OR (SILIcon adj nitride)) with plasma with CVD (terminat\$6)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/08/06 11:31
S48	332	S47 and @pd>"20081001"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/08/06 11:18
S47	5875	S44 or S45 or S46	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/08/06 11:18
S46	1430	257/409,488-490.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/08/06 11:18

S45	755	257/339.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/08/06 11:18
S44	4054	257/139,212,34,401,630,646,649.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/08/06 11:18

6/16/2010 10:22:26 PM

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